

3-phase Brushless Motor Driver IC for Automotive SPF6102

Sanken

Data Sheet

Description

The SPF6102 is 3-phase Brushless Motor Driver IC. The IC is suitable for the applications which the maximum applied voltage to the motor is 150 V or less.

The IC is driven by a bootstrap circuit, and the charge to this boost power supply (boot capacitor) is supplied from the internal auxiliary power supply. This auxiliary power supply is boosted by the internal charge pump circuit and supplies a stable voltage that does not depend on the automotive inherent battery variation to the gate drive circuit.

The IC uses the compact SMD package, HSOP48 with high thermal dissipation and provides high-density mounting. Since the IC has the various protection functions, it can drive 3-phase brushless motor with few external components.

Package

HSOP48



Not to scale

Features

- AEC-Q100 Qualified
- Built-in Bootstrap Diode
- Built-in Auxiliary Power Supply (VREGx)
- Bare Lead Frame: Pb-free (RoHS compliant)
- Enable Function
(All phases shutdown with EN = logic low)
- Fault Signal Output at Protect Circuit Activated
- Protections
 - Simultaneous On-state Prevention
 - VBB Pin Overvoltage Protection (VBB_OVP): Auto-restart
 - Undervoltage Lockout
VBB Pin (VBB_UVLO): Auto-restart
VDD Pin (VDD_UVLO): Auto-restart
VREGx Pin (VREGx_UVLO): Auto-restart
 - Thermal Shutdown (TSD)

Specifications

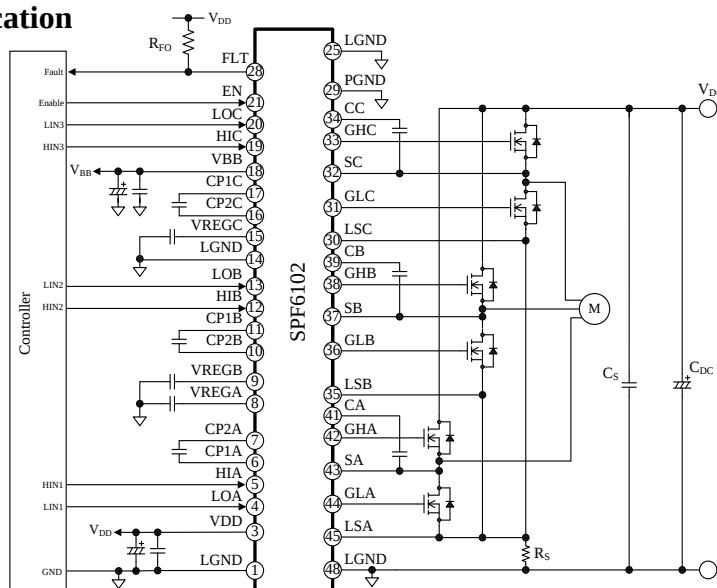
- Maximum Main Supply Voltage: $V_{DC} = 150\text{ V}$
- Maximum Logic Supply Voltage: $V_{BB} = 35\text{ V}$
- Typical On-resistance of Internal Drive Circuit
 - Sink: $4\ \Omega$
 - Source: $5\ \Omega$

Applications

For driving DC brushless motor such as:

- Inverter
- Onboard Charger (OBC)
- Battery Management System (BMS)

Typical Application



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1. Absolute Maximum Ratings

Current polarities are defined as follows: current going into the IC (sinking) is positive current (+); and current coming out of the IC (sourcing) is negative current (–).

Unless specifically noted, $T_A = 25\text{ }^{\circ}\text{C}$, and reference ground is the LGND pin.

Parameter	Symbol	Conditions	Ratings	Unit
Direct Current Input Voltage	V_{BB1}		–0.6 to 35	V
	V_{BB2}	$T < 400\text{ ms}$	40	V
VREGx Pin Voltage	V_{REG}		–0.6 to 18	V
VDD Pin Voltage	V_{DD}		–0.3 to 6	V
HLx, LOx and EN Pin Voltage	V_{IN}		–0.3 to 6	V
LSx Pin Voltage	V_{LSx}		–4 to 4	V
GLx Pin Voltage	V_{GLx}		–4 to 18	V
Sx Pin Voltage	V_{Sx}		–4 to 132	V
GHx Pin Voltage	V_{GHx}		–4 to 150	V
Cx Pin Voltage	V_{Cx}		–0.3 to 150	V
FLT Pin Voltage	V_{FLT}		–0.3 to 6	V
CP1x Pin Voltage	V_{CP1x}		–0.3 to 18	V
CP2x Pin Voltage	V_{CP2x}		–0.3 to 18	V
Power Dissipation	P_{D1}	Infinite Heatsink	30.4	W
	P_{D2}	Glass-epoxy Board*	3.57	W
Junction Temperature	T_J		–40 to 150	$^{\circ}\text{C}$
Operating Ambient Temperature	T_{OP}		–40 to 105	$^{\circ}\text{C}$
Storage Temperature	T_{STG}		–40 to 150	$^{\circ}\text{C}$
Junction-to-Case Thermal Resistance	θ_{J-C}		4.1	$^{\circ}\text{C/W}$
Junction-to-Ambient Thermal Resistance	θ_{J-A}		35	$^{\circ}\text{C/W}$

* Board size is 50 mm × 74 mm, thickness of glass-epoxy is 1.6 mm, and thickness of copper laminate is 18 μm .

2. Recommended Operating Conditions

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
VBB Pin Input Supply Voltage	V_{BB}		7	14	18	V
VDD Pin Input Supply Voltage	V_{DD}		4.5	5.0	5.5	V

3. Electrical Characteristics

Current polarities are defined as follows: current going into the IC (sinking) is positive current (+); and current coming out of the IC (sourcing) is negative current (–).

Unless specifically noted, $T_A = -30\text{ }^{\circ}\text{C}$ to $125\text{ }^{\circ}\text{C}$, $V_{BB} = 14\text{ V}$, $V_{DD} = EN = 5\text{ V}$, $C_{REGx} = 10\text{ }\mu\text{F}$, $f_{PWM} = 22.5\text{ kHz}$, and $C_{Px} = C_{Bx} = 0.1\text{ }\mu\text{F}$.

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
VBB Input Current 1	I_{BB1}	$V_{DD} = EN = 0\text{ V}$ $HIx = LOx = 5\text{ V}$	—	5	—	mA
VBB Input Current 2	I_{BB2}	$HIx = LOx = 5\text{ V}$	—	15	—	mA
VDD Input Current	I_{DD}	$HIx = LOx = 5\text{ V}$	—	1.0	5.0	mA
Cx Pin, GHx Pin, Sx Pin Current	I_{CxL}	$Cx = GHx = Sx = 90\text{ V}$	—	—	100	μA
VREGx Output Voltage 1	V_{REGx1}	$7\text{ V} < V_{BB} < 8\text{ V}$	10	12	15	V
VREGx Output Voltage 2	V_{REGx2}	$8\text{ V} \leq V_{BB}$	12	15	18	V
Enable Voltage	V_{ENH}	$HIx = 5\text{ V}$, $LSx = Sx = LGND$	2.0	—	—	V
Enable Release Voltage	V_{ENL}		—	—	0.8	V
Enable Voltage Hysteresis	ΔV_{EN}		—	0.15	—	V
HIx Pin Logic Low Input Voltage	V_{HIxH}	$HIx = 5\text{ V}$, $LSx = Sx = LGND$	—	—	0.8	V
HIx Pin Logic High Input Voltage	V_{HIxL}		2.0	—	—	V
HIx Pin Input Voltage Hysteresis	ΔV_{HIx}		—	0.15	—	V
LOx Pin Logic Low Input Voltage	V_{LOxH}	$LOx = 5\text{ V}$, $LSx = Sx = LGND$	—	—	0.8	V
LOx Pin Logic High Input Voltage	V_{LOxL}		2.0	—	—	V
LOx Pin Input Voltage Hysteresis	ΔV_{LOx}		—	0.15	—	V
EN Pin Input Current (H)	I_{ENH}	$EN = 5\text{ V}$	—	100	500	μA
EN Pin Input Current (L)	I_{ENL}	$EN = 0\text{ V}$	–100	—	—	μA
HIx Pin Input Current (H)	I_{HIxH}	$HIx = 0\text{ V}$	–500	–100	—	μA
HIx Pin Input Current (L)	I_{HIxL}	$HIx = 5\text{ V}$	—	—	100	μA
LOx Pin Input Current (H)	I_{LOxH}	$LOx = 0\text{ V}$	–500	–100	—	μA
LOx Pin Input Current (L)	I_{LOxL}	$LOx = 5\text{ V}$	—	—	100	μA
FLT Pin Output Saturation Voltage	V_{FLT}	$I_{FLT(L)} = 1\text{ mA}$	—	—	0.4	V
Bootstrap Diode Forward Voltage	$V_{TH(BD)}$	$I_F = 1\text{ mA}$	0.4	1.2	1.7	V
GHx Pin Source On-resistance	$R_{DS(SC_GHx)}$	$HIx = 0\text{ V}$, $LOx = 5\text{ V}$, $LSx = Sx = LGND$, $Cx > 10\text{ V}$, $V_{REGx} > 10\text{ V}$	3	5.0	10	Ω
GHx Pin Sink On-resistance	$R_{DS(SI_GHx)}$		2	4.0	8	Ω
GLx Pin Source On-resistance	$R_{DS(SC_GLx)}$	$HIx = 5\text{ V}$, $LOx = 0\text{ V}$, $LSx = Sx = LGND$, $Cx > 10\text{ V}$, $V_{REGx} > 10\text{ V}$	3	5.0	10	Ω
GLx Pin Sink On-resistance	$R_{DS(SI_GLx)}$		2	4.0	8	Ω
High-side Output Delay Time	$t_{on(H)x}$	$C_{iss} = 3300\text{ pF}$, see Figure 3-1	—	250	—	ns
	$t_{off(H)x}$		—	200	—	ns
Low-side Output Delay Time	$t_{on(L)x}$	$C_{iss} = 3300\text{ pF}$, see Figure 3-1	—	250	—	ns
	$t_{off(L)x}$		—	200	—	ns

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
GHx Pin Output Rise Time ⁽¹⁾	$t_{r(GHx)}$	20% V_{GHx} to 80% V_{GHx} , Ciss = 3300 pF, see Figure 3-1	10	—	100	ns
GHx Pin Output Fall Time ⁽¹⁾	$t_{f(GHx)}$		10	—	100	ns
GLx Pin Output Rise Time ⁽¹⁾	$t_{r(GLx)}$	20% V_{GLx} to 80% V_{GLx} , Ciss = 3300 pF, see Figure 3-1	10	—	100	ns
GLx Pin Output Fall Time ⁽¹⁾	$t_{f(GLx)}$		10	—	100	ns
VDD Pin Undervoltage Lockout Release Voltage	$V_{UVDD(H)}$		—	4.0	—	V
VDD Pin Undervoltage Lockout Operating Voltage	$V_{UVDD(L)}$		—	3.8	—	V
VDD Pin Undervoltage Lockout Hysteresis	ΔV_{UVDD}		—	0.2	—	V
VBB Pin Overvoltage Protection Operating Voltage	$V_{OVBB(H)}$		—	28	—	V
VBB Pin Overvoltage Protection Release Voltage	$V_{OVBB(L)}$		—	25	—	V
VBB Pin Overvoltage Protection Hysteresis	ΔV_{OVBB}		—	3	—	V
VBB Pin Undervoltage Lockout Release Voltage	$V_{UVBB(H)}$		6.0	6.5	7.0	V
VBB Pin Undervoltage Lockout Operating Voltage	$V_{UVBB(L)}$		5.5	6.1	6.6	V
VBB Pin Undervoltage Lockout Hysteresis	ΔV_{UVBB}		—	0.4	—	V
VREGx Pin Undervoltage Lockout Release Voltage	$V_{UVREGx(H)}$		6.5	7.5	8.5	V
VREGx Pin Undervoltage Lockout Operating Voltage	$V_{UVREGx(L)}$		6.0	7.1	8.2	V
VREGx Pin Undervoltage Lockout Hysteresis	ΔV_{UVREGx}		—	0.4	—	V
Thermal Shutdown Starting Temperature ⁽²⁾	T_{TSD}		151	—	—	°C

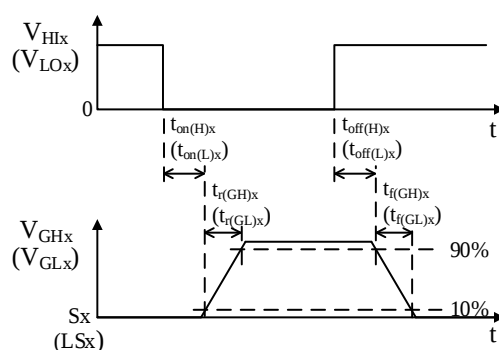


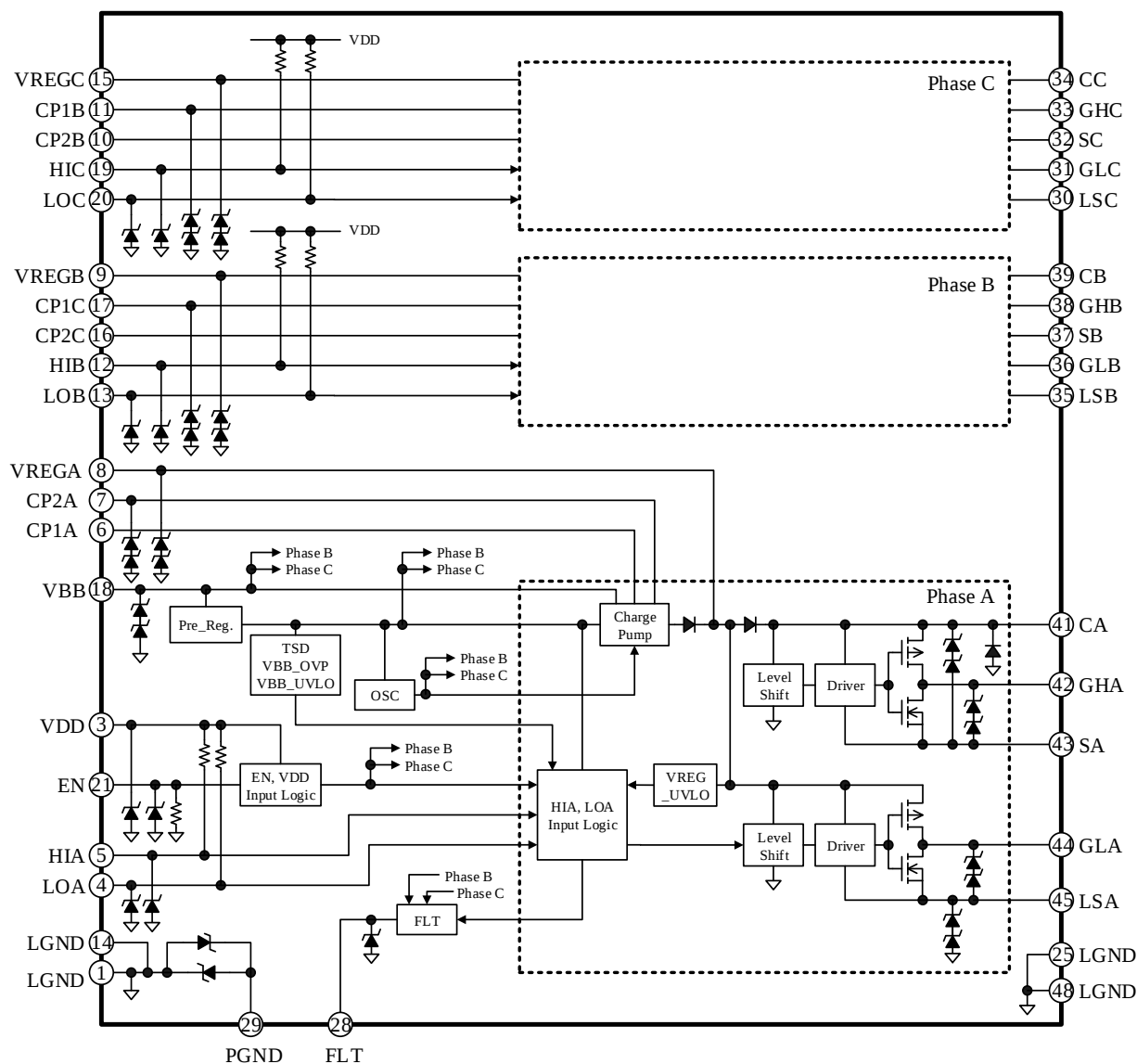
Figure 3-1. Definition of Switching Time

⁽¹⁾ When the outputs of the GHx and GLx pins are turned on/ off, the typical design values of output pulse current of the GHx and GLx pins are as follows (conditions: VREGx = 15 V, $t < 100$ ns, and $T_A = 25$ °C):

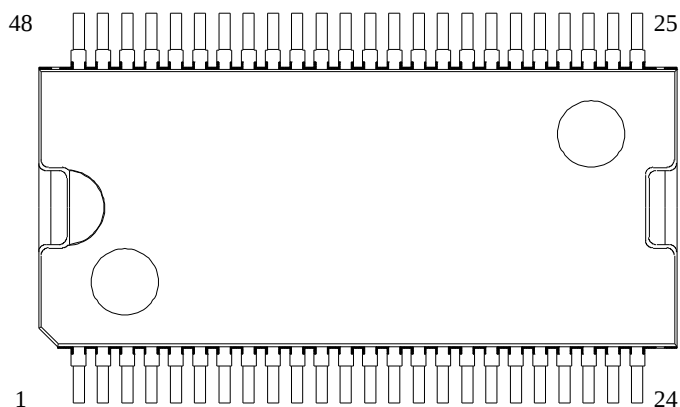
- Turning on: $I_{SOURCE} = 2.0$ A
- Turning off: $I_{SINK} = 2.3$ A

⁽²⁾ It is guaranteed by design. The typical design value of thermal shutdown starting temperature is 165 °C.

4. Block Diagram



5. Pin Configuration Definitions



Pin Number	Pin Name	Function	Pin Number	Pin Name	Function
1	LGND	Control ground	25	LGND	Control ground
2	(NC)	(No connection)	26	(NC)	(No connection)
3	VDD	Logic supply input for input signal	27	(NC)	(No connection)
4	LOA	Low-side logic input for A-phase	28	FLT	Fault signal output (Open drain)
5	HIA	High-side logic input for A-phase	29	PGND	Power ground
6	CP1A	Capacitor connect pin 1 for A-phase charge pump circuit	30	LSC	C-phase low-side source connection
7	CP2A	Capacitor connect pin 2 for A-phase charge pump circuit	31	GLC	C-phase low-side gate drive signal output
8	VREGA	Capacitor connect pin for A-phase high- and low-side gate drive	32	SC	C-phase high-side source connection
9	VREGB	Capacitor connect pin for B-phase high- and low-side gate drive	33	GHC	C-phase high-side gate drive signal output
10	CP2B	Capacitor connect pin 2 for B-phase charge pump circuit	34	CC	C-phase boot capacitor connection
11	CP1B	Capacitor connect pin 1 for B-phase charge pump circuit	35	LSB	B-phase low-side source connection
12	HIB	High-side logic input for B-phase	36	GLB	B-phase low-side gate drive signal output
13	LOB	Low side logic input for B-phase	37	SB	B-phase high-side source connection
14	LGND	Control ground	38	GHB	B-phase high-side gate drive signal output
15	VREGC	Capacitor connect pin for C-phase high- and low-side gate drive	39	CB	B-phase boot capacitor connection
16	CP2C	Capacitor connect pin 2 for C-phase charge pump circuit	40	(NC)	(No connection)
17	CP1C	Capacitor connect pin 1 for C-phase charge pump circuit	41	CA	A-phase boot capacitor connection
18	VBB	Main supply input	42	GHA	A-phase high-side gate drive signal output
19	HIC	High side logic input for C-phase	43	SA	A-phase high-side source connection
20	LOC	Low side Logic input for C-phase	44	GLA	A-phase low-side gate drive signal output
21	EN	Enable signal input	45	LSA	A-phase low-side source connection
22	(NC)	(No connection)	46	(NC)	(No connection)
23	(NC)	(No connection)	47	(NC)	(No connection)
24	(NC)	(No connection)	48	LGND	Control ground

If the GLx pin voltage becomes lower by about 0.6 V to 1.8 V than the LSx pin voltage, the IC may be damaged. To avoid the situation, a diode, D_{GLx}, must be added between the GLx pin and the LSx pin.

D_S and D_{Gx} must be placed near the IC, and connected with a minimal length of traces.

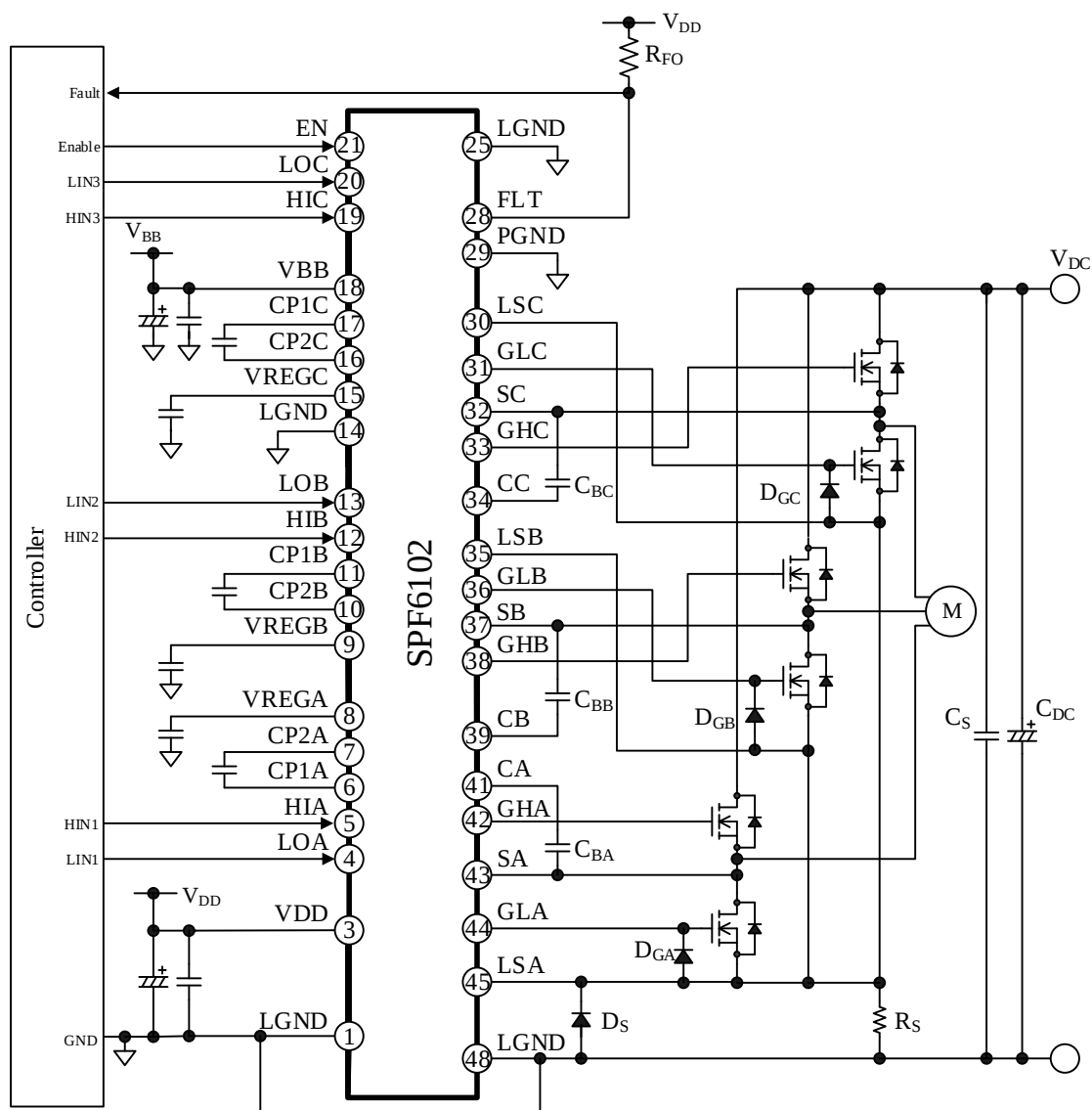


Figure 6-1. Typical Application

7. Truth Table

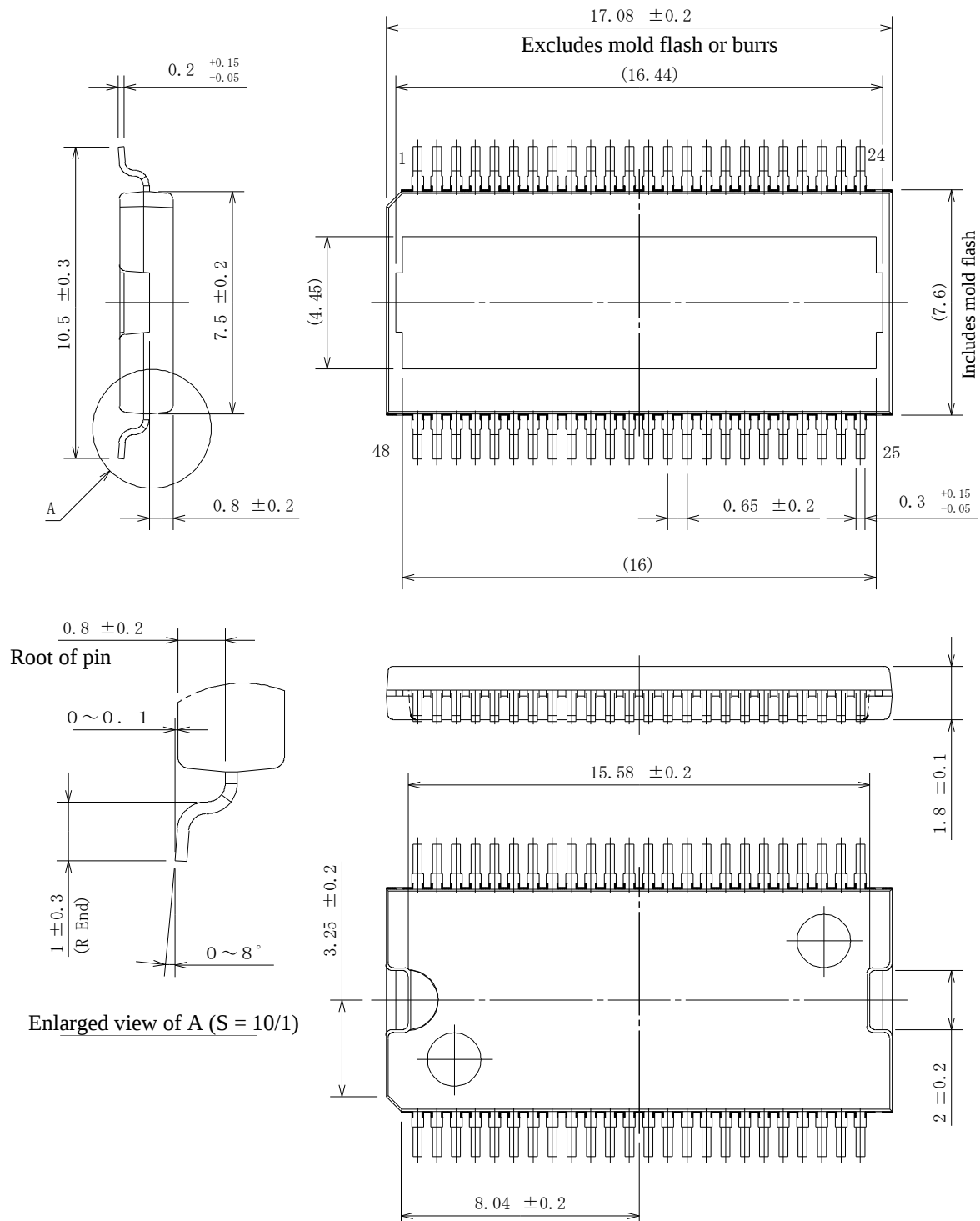
Table 7-1. Truth Table for Operation Modes

Mode	Input Pin		Output Pin			Remarks
	HIx	LOx	GHx	GLx	FLT*	
Normal Operation	H	H	L	L	H	
	L	H	H	L	H	
	H	L	L	H	H	
	L	L	L	L	H	Simultaneous On-state Prevention
VBB Pin Undervoltage Lockout (VBB_UVLO)	H	H	L	L	L	
	L	H	L	L	L	
	H	L	L	L	L	
	L	L	L	L	L	
VDD Pin Undervoltage Lockout (VDD_UVLO)	H	H	L	L	L	
	L	H	L	L	L	
	H	L	L	L	L	
	L	L	L	L	L	
Enable Signal Input (EN pin is low level)	H	H	L	L	H	
	L	H	L	L	H	
	H	L	L	L	H	
	L	L	L	L	H	
VREGx Pin Undervoltage Lockout (VREGx_UVLO)	H	H	L	L	L	
	L	H	H	L	L	
	H	L	L	H	L	
	L	L	L	L	L	Simultaneous On-state Prevention
Thermal Shutdown (TSD)	H	H	L	L	L	
	L	H	L	L	L	
	H	L	L	L	L	
	L	L	L	L	L	

*The FLT pin is pulled up to the VDD pin.

8. Physical Dimensions

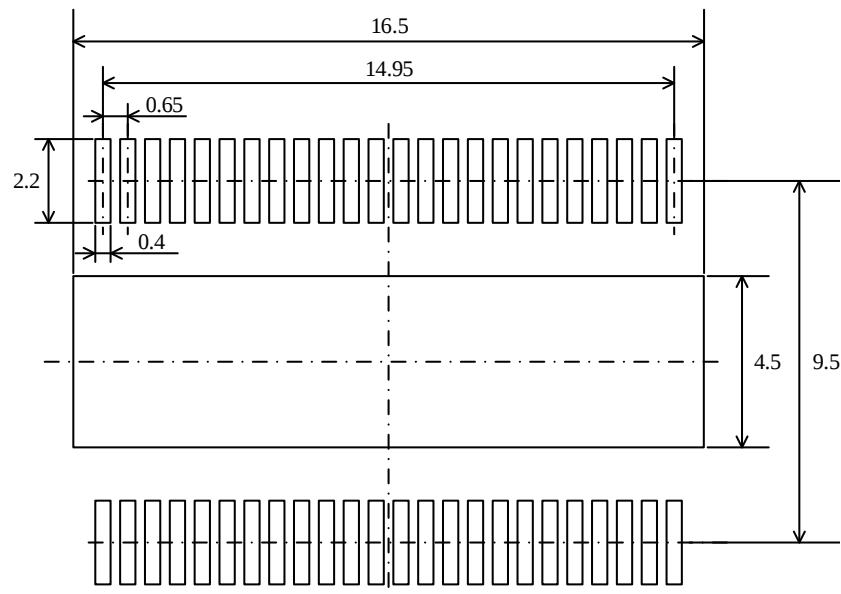
● HSOP48 Package



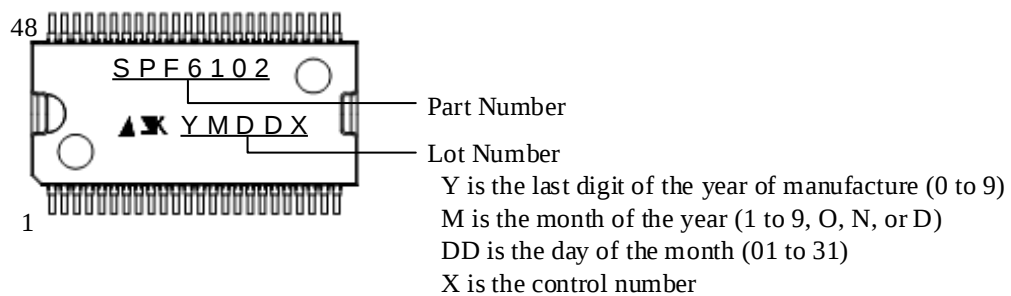
NOTES:

- Dimensions in millimeters
- Bare lead frame: Pb-free (RoHS compliant)

• HSOP48 Land Pattern Example



9. Marking Diagram



10. Operational Descriptions

All the characteristic values given in this section are typical values, unless they are specified as minimum or maximum. Current polarities are defined as follows: current going into the IC (sinking) is positive current (+); and current coming out of the IC (sourcing) is negative current (–).

For pin descriptions, this section employs a notation system that denotes a pin name or an electronic symbol name with the arbitrary letter “x”, depending on context. The A, B, and C phases of 3-phase motor are represented as the alphabets A, B, and C, respectively. Thus, “(the) H1x pin” is used when referring to either or all of the H1A, H1B, or H1C pin.

10.1. Pin Descriptions

10.1.1. VBB

This is the main supply input pin of the IC. Recommended applied voltage to the VBB pin is 7 V to 18 V.

When the same power supply is connected to the VBB pin and the external output transistors, power supply loop trace should be designed as wide and short as possible. A Bypass capacitor for noise reduction should be connected to the VBB pin as needed. The bypass capacitor should be placed near the VBB pin, and connected to the VBB pin with a minimal length of traces.

10.1.2. VDD

This is the supply input for input logic circuit. Recommended applied voltage to the VDD pin is 4.5 V to 5.5 V.

10.1.3. VREGx

The power supply of high- and low-side gate drive circuit is generated by the internal charge pump circuit. Thus, the gate can be driven stably even if the VBB pin voltage is low (7 V or more).

Capacitor (10 μ F or more is recommended) for holding supply voltage of gate drive circuit should be connected to the VREGx pin. External power supply connection is unnecessary.

10.1.4. CP1x and CP2x

Connect a capacitor for internal charge pump circuit between the CP1x pin and the CP2x pin. The recommended capacitance is 0.1 μ F.

10.1.5. Cx

Connect a high-side boot capacitor, C_{Bx} , between the Cx pin and the Sx pin. The recommended capacitance of C_{Bx} is 0.1 μ F or more. Since the capacitance depends on the drive frequency and control duty, the setting is required according to the application. For proper startup, turn on the low-side output transistors first, and then charge C_{Bx} up to its maximum capacity.

10.1.6. H1x and LOx

These are the signal input pins. The H1x pin acts as high-side controller whereas the LOx pin acts as low-side controller. Since the H1x and LOx pins incorporate a pull-up resistor, the initial state is high (see the block diagram in Section 4).

The width of the input signals to the H1x and LOx pins is required 500 ns or more.

Note that dead time setting for the input signals of the H1x and LOx pins must be done because the IC does not have a dead time generator. Dead time must be set so that the simultaneous on-state does not occur according to the output transistors to be used.

10.1.7. EN

When the high signal is input to the EN pin, all output signals of the GHx and GLx pins become logic low. Since the EN pin incorporates a pull-down resistor, the initial state is low (see the block diagram in Section 4).

10.1.8. FLT

This is the output pin of fault signal. Pull up the FLT pin because the FLT pin is open drain. When the FLT pin is pulled up to the power supply of 5 V, the recommended pull-up resistor is about 20 k Ω . The FLT pin logic level is high in normal operation, and becomes low when one or more the following protections are activated.

- VBB pin Overvoltage Protection (VBB_OVP)
- VBB pin Undervoltage Lockout (VBB_UVLO)
- VDD pin Undervoltage Lockout (VDD_UVLO)
- VREGx pin Undervoltage Lockout (VREGx_UVLO)
- Thermal Shutdown (TSD)

10.1.9. GHx and GLx

These are the gate drive outputs, and are connected to the gate of external output transistors. The GHx pin acts as high-side controller whereas the GLx pin acts as low-side controller. A pull-down resistor of 100 k Ω (typ.) and protection Zener diodes (the Zener diode) of 18 V (typ.) are internally connected between the GHx pin and

the Sx pin, and between the GLx pin and the LSx pin respectively (see Figure 10-1 and Figure 10-2).

When the current from motor flows to the forward direction of this Zener diode, this may be damaged. In the application that the current flows to the forward direction of the Zener diode, an external diode, D_{Gx} , must be added between the GHx pin and the Sx pin, and between the GLx pin and the LSx pin respectively (see Figure 6-1).

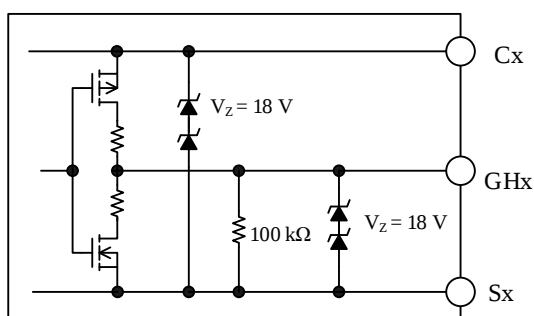


Figure 10-1. Internal Circuit of High-side Output

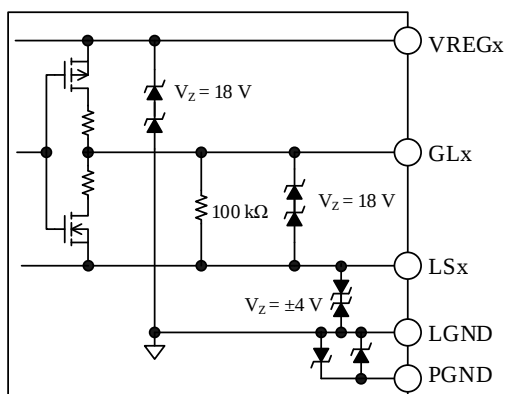


Figure 10-2. Internal Circuit of Low-side Output

10.1.10. Sx and SLx

Connect the Sx pin to the source pin of high-side output transistors and the drain pin of low-side output transistors, and the LSx pin to the source pin of low-side output transistors.

An ESD protection bidirectional Zener diode of ± 4 V is internally connected between the LSx pin and the LGND pin (see Figure 10-2). In the application that the voltage of ± 4 V or more is applied between the Sx pin and the LGND pin, the external diode, D_s , must be connected between the LSx pin and the LGND pin (see Figure 6-1).

10.1.11. LGND and PGND

The LGND pin is control ground of the IC. The PGND pin is power ground. A Zener diode is internally connected bidirectionally between the LGND pin and the PGND pin in parallel (see Figure 10-2).

10.2. Basic Operation

At startup, the voltage is applied to the VBB and VDD pins which are the power supply of the IC. Then, the high signal is input to the EN pin. After that, input the signal to the HIx and LOx pins; and on/off controls of the output transistors start.

When the low signal is input to the HIx pin, high-side gate output (the GHx pin) becomes logic high. When the low signal is input to the LO pin, low-side gate output (the GLx pin) becomes logic high (see Table 7-1).

The EN pin has an internally low-pass filter of 2.5 μ s for the noise malfunction prevention. The HIx and LOx pins do not have internal low-pass filter.

10.3. Simultaneous On-state Prevention

When the low signal is input to the HIx and LOx pins at once, the Simultaneous On-state Prevention is activated, and the outputs of the GHx and GLx pins become logic low. This prevents the breakdown of the output transistors.

10.4. Protections

The IC has the following protection functions.

When the following protections are activated, the outputs of the GHx and GLx pins become logic low, and stop the output transistors. In addition, the fault signal is output (the FLT pin logic level becomes low).

When the protection is released after the fault conditions are removed, the FLT output becomes logic high. Then, the GHx and GLx pins restart output the signals according to the input commands on the HIx and LOx pins from the next falling edge.

However, during VREGx_UVLO is activated, the IC outputs the fault signal with maintaining the outputs of the GHx and GLx pins according to input signal.

- VBB Pin Overvoltage Protection (VBB_OVP)
- VBB Pin Undervoltage Lockout (VBB_UVLO)
- VDD Pin Undervoltage Lockout (VDD_UVLO)
- VREGx Pin Undervoltage Lockout (VREGx_UVLO)
- Thermal Shutdown (TSD)

10.4.1. VBB Pin Overvoltage Protection (VBB_OVP)

When the VBB pin voltage increases to the VBB pin overvoltage protection operating voltage $V_{OVBB(H)} = 28$ V or more, VBB_OVP is activated. When the VBB pin voltage decreases to the release voltage $V_{OVBB(L)} = 25$ V or less, the IC returns to the normal operation.

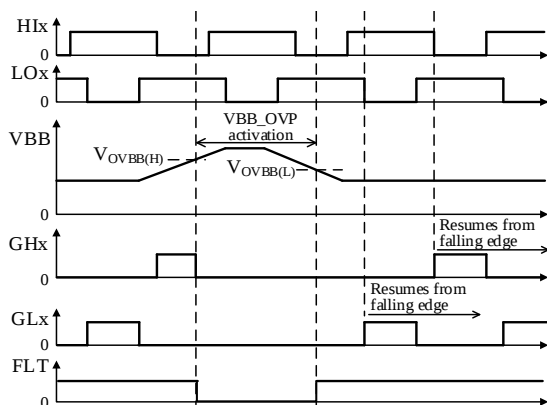


Figure 10-3. Operational Waveform of VBB_OVP

10.4.2. VBB Pin Undervoltage Lockout (VBB_UVLO)

The VBB pin voltage decrease to the VBB pin undervoltage lockout operating voltage $V_{UVBB(L)} = 6.1$ V or less, VBB_UVLO is activated. When the VBB pin voltage increases to the release voltage $V_{UVBB(H)} = 6.5$ V or more, the IC returns to the normal operation. During the VBB_UVLO activation, the internal charge pump circuit (OSC circuit operation is maintained) and the VREG pin boost operation are stopped.

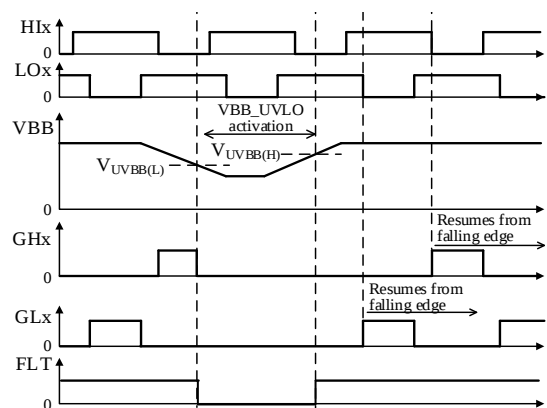


Figure 10-4. Operational Waveform of VBB_UVLO

10.4.3. VDD Pin Undervoltage Lockout (VDD_UVLO)

When the VDD pin voltage decreases to the VDD pin undervoltage lockout operating voltage $V_{UVDD(L)} = 3.8$ V or less, the VDD_UVLO is activated.

When the VDD pin voltage increases to the release voltage $V_{UVDD(H)} = 4.0$ V or more, the IC returns to the normal operation.

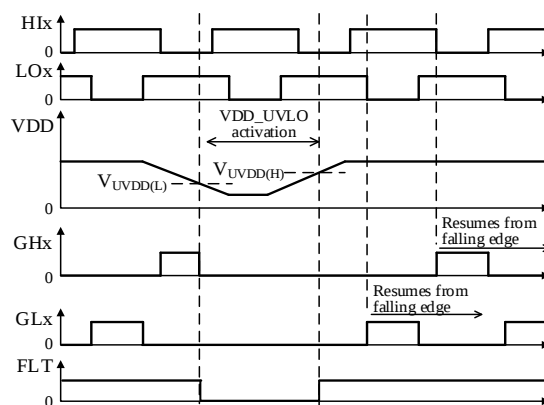


Figure 10-5. Operational Waveform of VDD_UVLO

10.4.4. VREGx Pin Undervoltage Lockout (VREGx_UVLO)

When the VREGx pin voltage decreases to VREGx pin undervoltage lockout operating voltage $V_{UVREGx(L)} = 7.1$ V or less due to the leak current of the capacitor connecting to the VREG pin, the VREGx_UVLO is activated.

When the VREG pin voltage increases to the release voltage $V_{UVREGx(H)} = 7.5$ V or more, the IC returns to the normal operation.

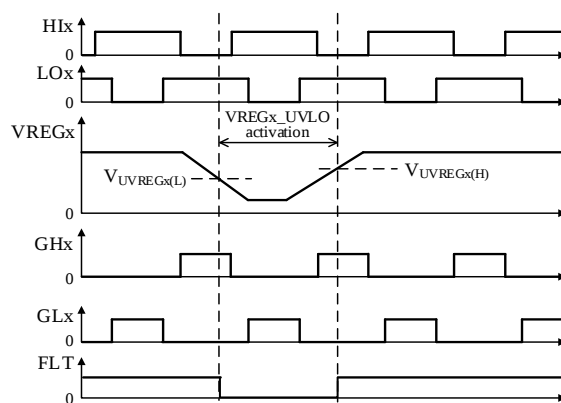


Figure 10-6. Operational Waveform of VREGx_UVLO

10.4.5. Thermal Shutdown (TSD)

When the junction temperature of the IC increases to $T_{TSD} = 151\text{ }^{\circ}\text{C}$ (min.) or more, the TSD is activated. The design value of TSD operating temperature is $165\text{ }^{\circ}\text{C}$ (typ.). TSD has the temperature hysteresis. When the temperature decreases by about $10\text{ }^{\circ}\text{C}$ from the junction temperature of TSD operation, TSD is released, and the IC returns to the normal operation.

TSD protects the IC against instantaneous heat generation, and does not guarantee the operation including reliability for a state that the heat generation continues for a long time.

10.5. Enable Function

The IC has an enable function.

When the low signal (0.8 V or less) is input to the EN pin, the input signals of the GHx and GLx pins become logic low. When the high signal (2.0 V or more) is input to the EN pin, the GHx and GLx pins restart output the signals according to the input commands on the Hix and LOx pins from the next falling edge. During the EN pin logic is low, the FLT pin logic level is maintained high.

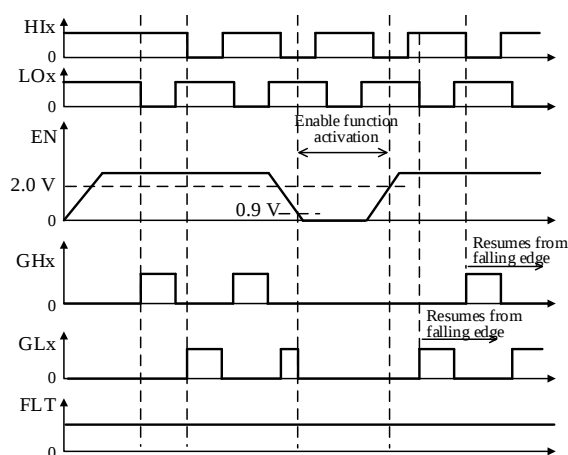


Figure 10-7 Operational Waveform of Enable Function

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